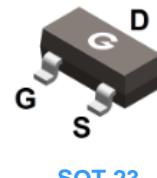
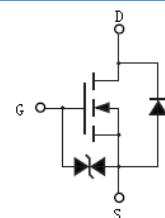


Features

- Fast switching speed
- HBM: JESD22-A114-B: class 2
- RoHS compliant with Halogen-free

HF



SOT-23

Mechanical Data

- Case: SOT-23
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
BSS138BK	SOT-23	3000 pcs / Tape & Reel	138BK

Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value		Unit
Drain-to-Source Voltage	V_{DSS}	60		V
Gate-to-Source Voltage	V_{GSS}	± 20		V
Continuous Drain Current ($T_A = 25^\circ\text{C}$) *1	I_D	500		mA
Continuous Drain Current ($T_A = 70^\circ\text{C}$) *1		400		mA
Pulsed Drain Current ($t_p = 10\mu\text{s}$, $T_A = 25^\circ\text{C}$)	I_{DM}	3000		mA
Power Dissipation ($T_A = 25^\circ\text{C}$) *1	P_D	370		mW
Operating Junction Temperature Range	T_J	-55 ~ +150		°C
Storage Temperature Range	T_{STG}	-55 ~ +150		°C

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Air *1	$R_{\theta JA}$	-	310	335	°C/W

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	60	-	-	V
$I_{DS(on)}$	Zero Gate Voltage Drain Current	$V_{DS} = 60\text{V}, V_{GS} = 0\text{V}$	-	-	1	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$	-	-	± 10	μA
On Characteristics						
$R_{DS(on)}$	Static Drain-Source On-resistance ^{*2}	$V_{GS} = 10\text{V}, I_D = 0.5\text{A}$	-	0.56	0.7	Ω
		$V_{GS} = 4.5\text{V}, I_D = 0.2\text{A}$	-	0.64	1.2	
		$V_{GS} = 2.5\text{V}, I_D = 0.1\text{A}$	-	0.92	3	
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	0.8	1.0	1.5	V
R_G	Gate Resistance	$V_{GS} = 0\text{V}, f = 1\text{MHz}$	-	42	-	Ω
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$ $V_{DS} = 30\text{V}$ $f = 1.0\text{MHz}$	-	65	-	pF
C_{oss}	Output Capacitance		-	12	-	
C_{rss}	Reverse Transfer Capacitance		-	7	-	
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time ^{*3}	$V_{DD} = 30\text{V}$ $V_{GS} = 10\text{V}$ $I_D = 0.36\text{A}$ $R_G = 6\Omega$	-	2	-	ns
t_r	Turn-on Rise Time ^{*3}		-	19	-	
$t_{d(off)}$	Turn-Off Delay Time ^{*3}		-	6	-	
t_f	Turn-Off Fall Time ^{*3}		-	23	-	
Q_G	Total Gate-Charge	$V_{DS} = 30\text{V}$ $V_{GS} = 4.5\text{V}$ $I_D = 0.2\text{A}$	-	2.3	-	nC
Q_{GS}	Gate to Source Charge		-	0.6	-	
Q_{GD}	Gate to Drain (Miller) Charge		-	0.5	-	
Source-Drain Diode Characteristics						
V_{SD}	Diode Forward Voltage ^{*2}	$I_S = 0.5\text{A}, V_{GS} = 0\text{V}$	-	0.8	1.4	V

Notes:

- The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper
- The data tested by pulsed, pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- Guaranteed by design, not subject to production

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

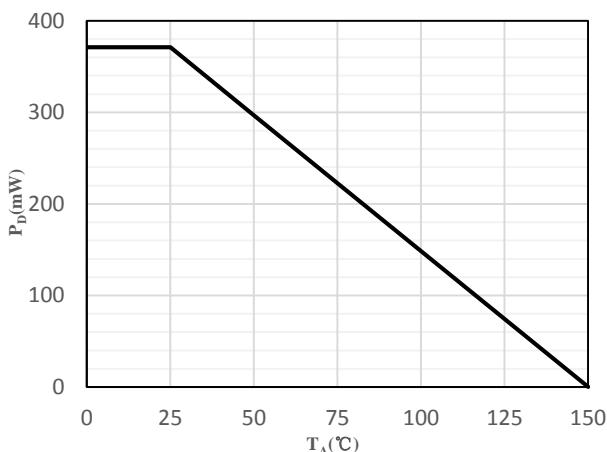


Fig 1 Power Dissipation

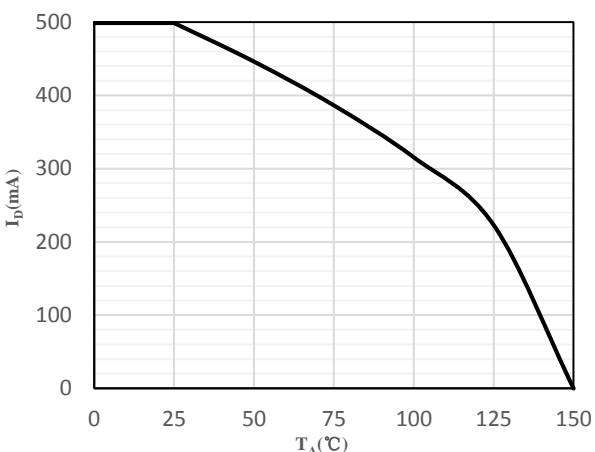


Fig 2 Drain Current

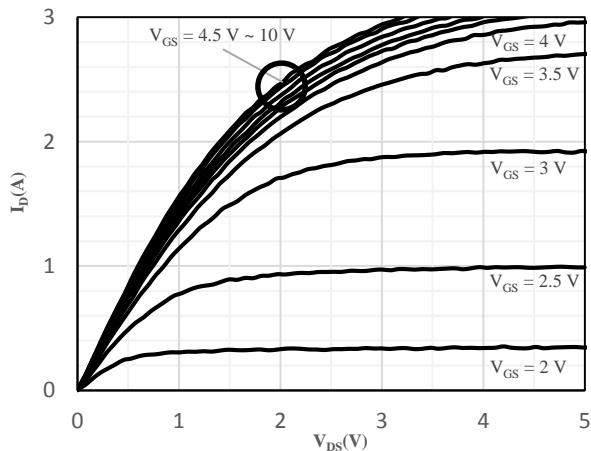


Fig 3 Typical Output Characteristics

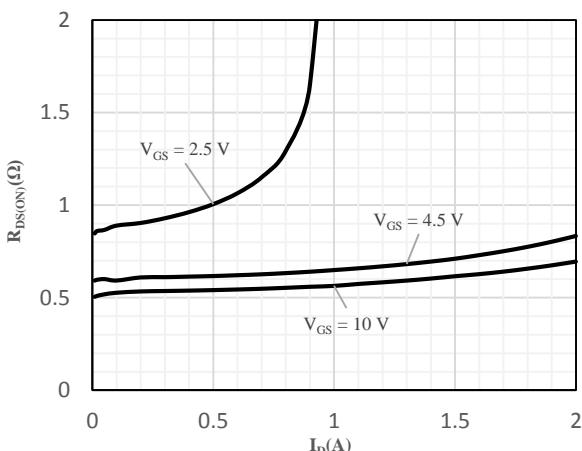


Fig 4 On-Resistance vs. Drain Current and Gate Voltage

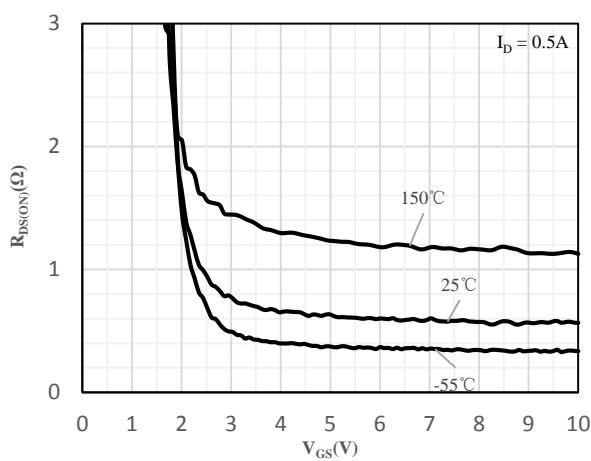


Fig 5 On-Resistance vs. Gate-Source Voltage

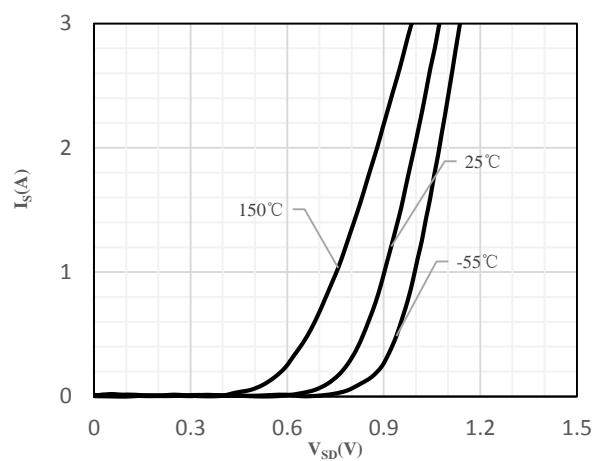


Fig 6 Body-Diode Characteristics

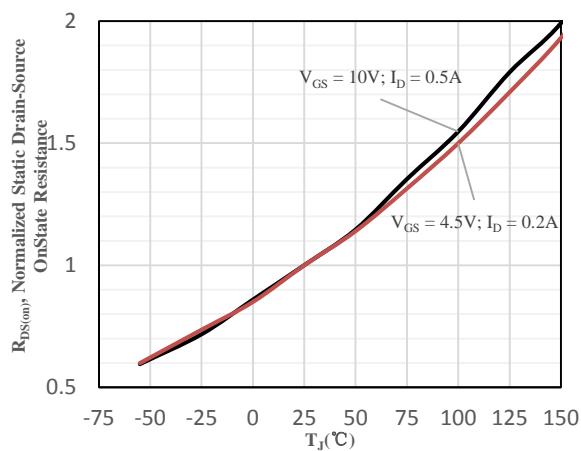


Fig 7 Normalized On-Resistance vs. Junction Temperature

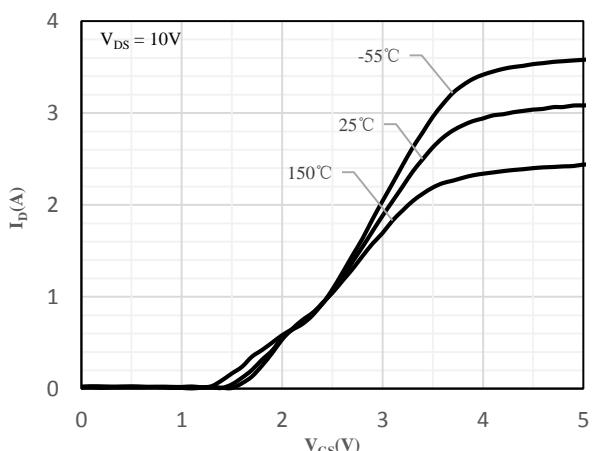


Fig 8 Transfer Characteristics

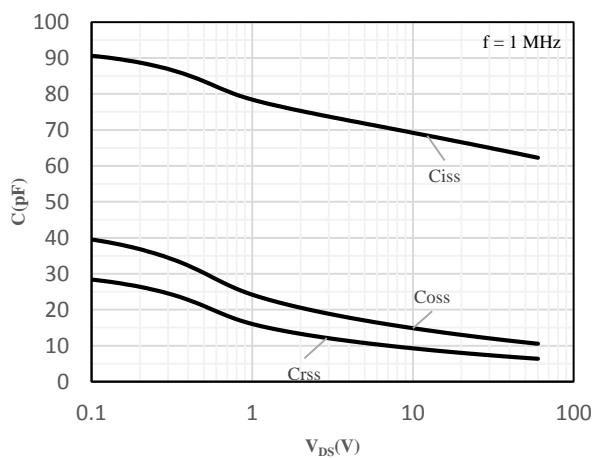


Fig 9 Capacitance Characteristics

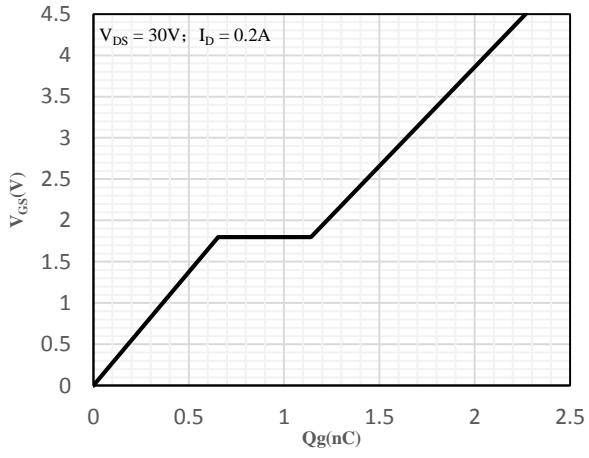


Fig 10 Gate-Charge Characteristics

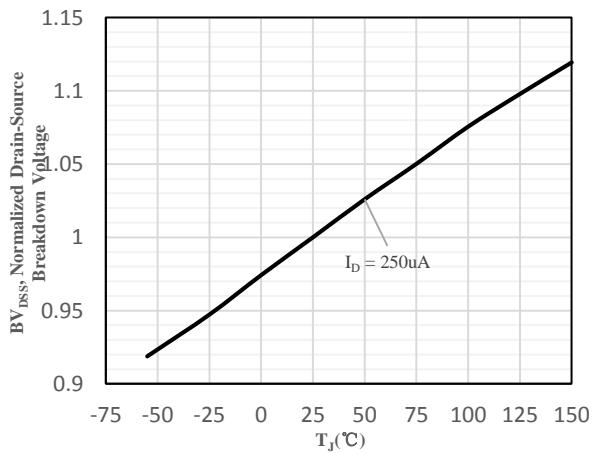


Fig 11 Normalized Breakdown Voltage vs. Junction Temperature

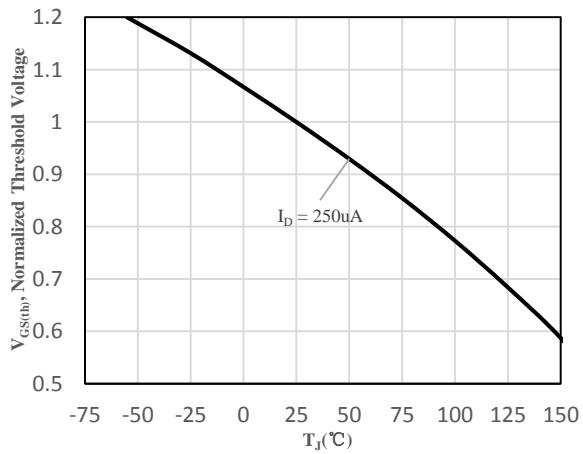


Fig 12 Normalized $V_{GS(th)}$ vs. Junction Temperature

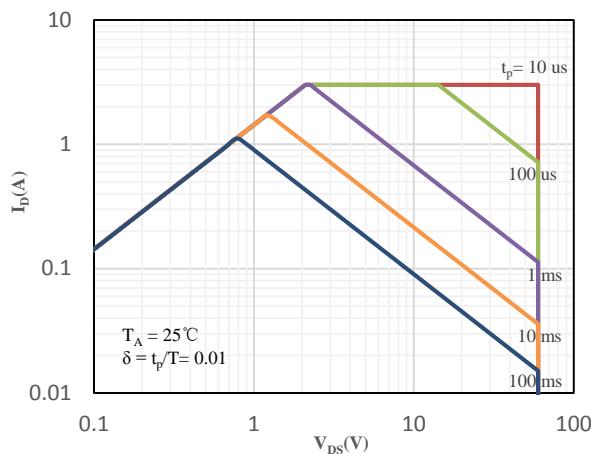


Fig 13 Safe Operation Area

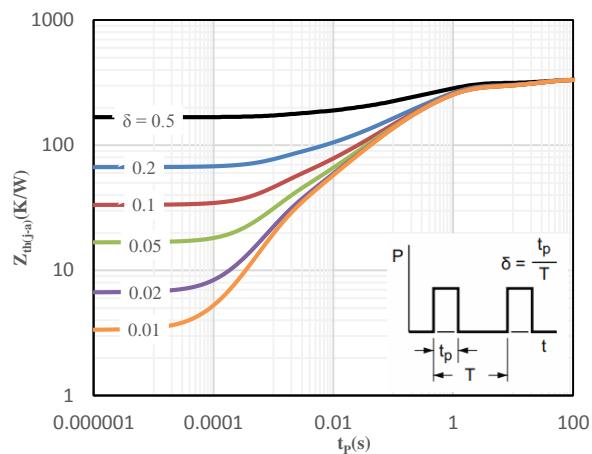
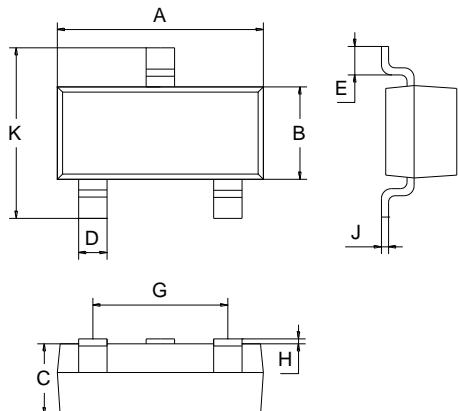


Fig 14 Maximum transient thermal impedance

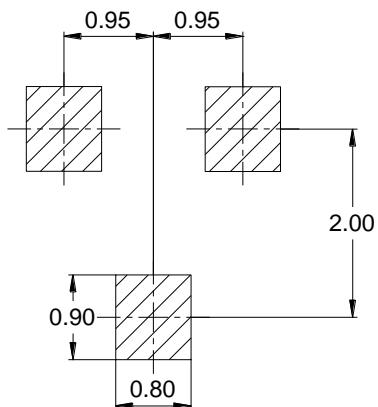
Package Outline Dimensions (Unit: mm)



SOT-23		
Dimension	Min.	Max.
A	2.70	3.10
B	1.10	1.50
C	0.90	1.10
D	0.30	0.50
E	0.35	0.48
G	1.80	2.00
H	0.02	0.10
J	0.05	0.15
K	2.20	2.60

Package Outline Dimensions (Unit: mm)

SOT-23



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